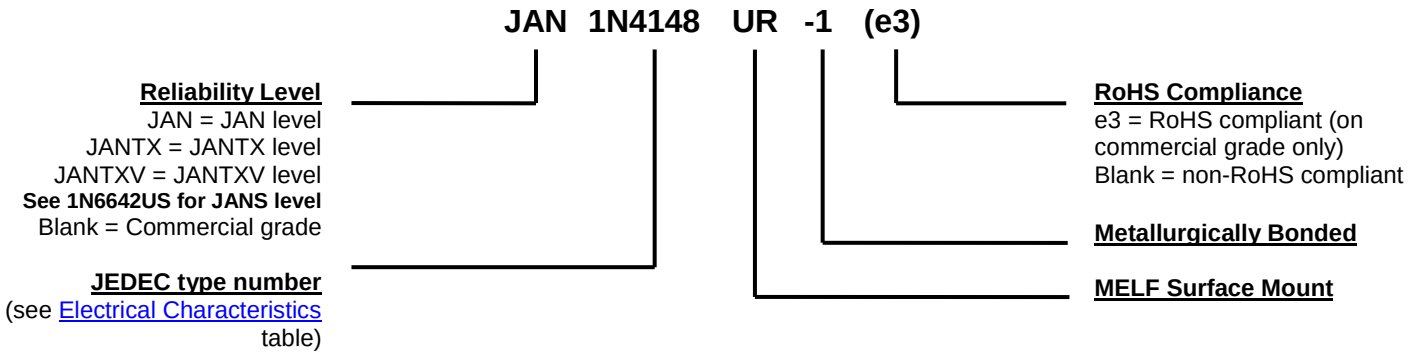
MECHANICAL and PACKAGING

- CASE: Hermetically sealed glass case package.
- TERMINALS: Tin/lead plated or RoHS compliant matte-tin (on commercial grade only) over copper clad steel. Solderable per MIL-STD-750, method 2026.
- POLARITY: Cathode end is banded.
- MOUNTING: The axial coefficient of expansion (COE) of this device is approximately +6PPM/°C. The COE of the mounting surface system should be selected to provide a suitable match with this device.
- MARKING: Part number.
- TAPE & REEL option: Standard per EIA-296. Consult factory for quantities.
- WEIGHT: 0.2 grams.
- See Package Dimensions on last page.

PART NOMENCLATURE



SYMBOLS & DEFINITIONS

Symbol	Definition
I_R	Reverse Current: The maximum reverse (leakage) current that will flow at the specified voltage and temperature.
I_O	Average Rectified Forward Current: The output current averaged over a full cycle with a 50 Hz or 60 Hz sine-wave input and a 180 degree conduction angle.
t_{rr}	Reverse Recovery Time: The time interval between the instant the current passes through zero when changing from the forward direction to the reverse direction and a specified decay point after a peak reverse current occurs.
V_F	Forward Voltage: The forward voltage the device will exhibit at a specified current (typically shown as maximum value).
V_R	Reverse Voltage: The reverse voltage dc value, no alternating component.
V_{RWM}	Working Peak Reverse Voltage: The maximum peak voltage that can be applied over the operating temperature range excluding all transient voltages (ref JESD282-B). Also sometimes known as PIV.

ELECTRICAL CHARACTERISTICS @ 25 °C unless otherwise noted

FORWARD VOLTAGE V_{F1} @ I_F=10 mA	FORWARD VOLTAGE V_{F2} @ I_F=100 mA	REVERSE RECOVERY TIME t_{rr} (Note 1)	FORWARD RECOVERY TIME t_{fr} (Note 2)	REVERSE CURRENT I_{R1} @ 20 V	REVERSE CURRENT I_{R2} @ 75 V	REVERSE CURRENT I_{R3} @ 20 V T_A=150°C	REVERSE CURRENT I_{R4} @ 75 V T_A=150°C	CAPACITANCE C (Note 3)	CAPACITANCE C (Note 4)
V	V	ns	ns	nA	µA	µA	µA	pF	pF
0.8	1.2	5	20	25	0.5	35	75	4.0	2.8

NOTE 1: $I_F = I_R = 10$ mA, $R_L = 100$ Ohms.
NOTE 2: $I_F = 50$ mA.
NOTE 3: $V_R = 0$ V, f = 1 MHz, $V_{SIG} = 50$ mV (pk to pk).
NOTE 4: $V_R = 1.5$V, f = 1 MHz, $V_{SIG} = 50$ mV (pk to pk).

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GRAPHS

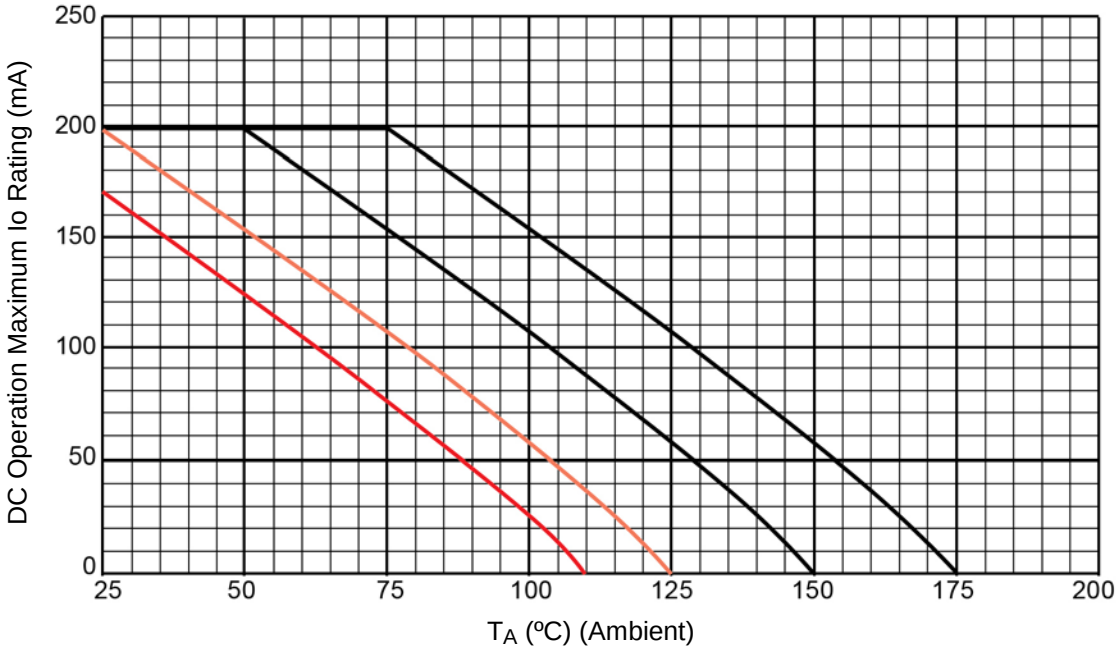

FIGURE 1 – Temperature – Current Derating

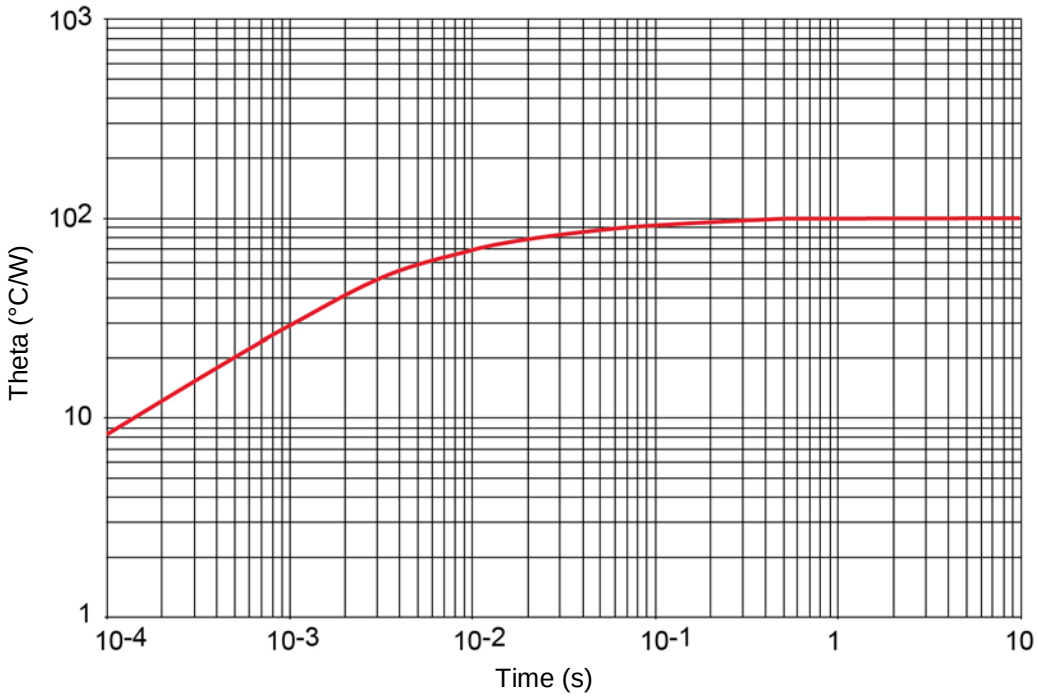

FIGURE 2 – Thermal Impedance

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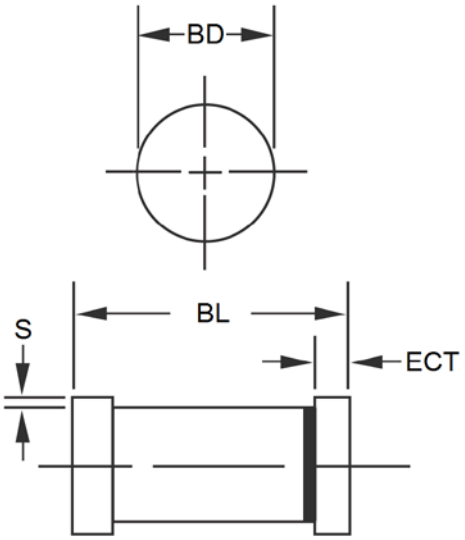
PACKAGE DIMENSIONS

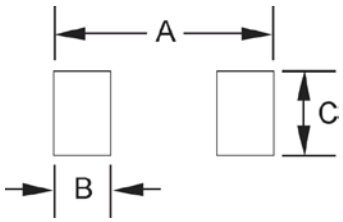


DIM	INCH		MILLIMETERS	
	MIN	MAX	MIN	MAX
BD	0.063	0.067	1.60	1.70
BL	0.130	0.146	3.30	3.71
ECT	0.016	0.022	0.41	0.56
S	.001 min		0.03 min	

NOTES:

1. Dimensions are in inches. Millimeters are given for general information only.
2. Dimensions are pre-solder dip.
3. Referencing to dimension S, minimum clearance of glass body to mounting surface on all orientations.
4. In accordance with ASME Y14.5M, diameters are equivalent to Φx symbology.

PAD LAYOUT



	INCH	mm
A	.200	5.08
B	.055	1.40
C	.080	2.03

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